



7th IEEE Electron Devices Technology and Manufacturing (EDTM) Conference 2023

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42A. Power Devices and Widebandgap Heterostructures (3)

Session Date:	March 9(Thu.), 2023
Session Time:	16:30-18:05
Session Room:	Room A (#301)
Session Chair:	Prof. Jungwoo Oh (Yonsei University) Prof. Man Hoi Wong (The Hong Kong University of Science and Technology)

[42A-1] [Invited]

16:30-16:55

Deep Insights into Recessed-Gate MOS-HEMT Technology for Power Applications

B. Mohamad, C. Le Royer, F. Rigaud-Minet, C. Piotrowicz, P. Fernandes Paes Pinto Rocha, C. Leurquin, W. Vandendaele, R. Escoffier, J. Buckley, S. Bécu, J. Biscarrat and R. Gwoziecki
Université Grenoble Alpes

[42A-2] [Invited]

16:55-17:20

Vertical GaN Power Devices

Wenwen Li and Dong Ji
The Chinese University of Hong Kong

[42A-3]

17:20-17:35

Effect of Parasitic Leakage Currents Associated with the Regrown Aperture of AlGaIn/GaN Current Aperture Vertical Electron Transistors (CAVETs)

Sara Pouladi and Jae Hyun Ryou
University of Houston

[42A-4]

17:35-17:50

Fabrication of AlGaIn/GaN MIS-HEMTs with Post-Growth Annealing

Meihua Liu^{1,2}, Yong Zhang¹ and Guoyong Huang²
¹Shenzhen Institute of Advanced Technology, ²SMiT

[42A-5]

17:50-18:05

A Width-Scalable SPICE Model of GaN-HEMTs for X-Band RF Applications

Md Hasnain Ansari¹, Raghvendra Dangi¹, Ahtisham Pampori¹, Pragya Kushwaha², Ekta Yadav², Santanu Sinha² and Yogesh Singh Chauhan¹
1Indian Institute of Technology Kanpur, 2Indian Space Research Organisation